

# DTB713Z series

PNP -200mA -30V Digital Transistors (Bias Resistor Built-in Transistors) Datasheet

Parameter	Value
V <sub>CC</sub>	-30V
I <sub>C(MAX.)</sub>	-200mA
R <sub>1</sub>	1.0kΩ
R <sub>2</sub>	10kΩ

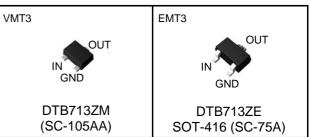
#### Features

- 1) Built-In Biasing Resistors
- Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors (see inner circuit).
- The bias resistors consist of thin-film resistors with complete isolation to allow negative biasing of the input. They also have the advantage of completely eliminating parasitic effects.
- 4) Only the on/off conditions need to be set for operation, making the circuit design easy.
- 5) Complementary NPN Types :DTD713Z series
- 6) Lead Free/RoHS Compliant.

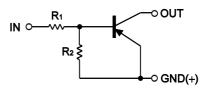
#### Application

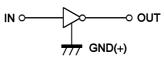
Switching circuit, Inverter circuit, Interface circuit, Driver circuit

#### Outline



#### Inner circuit





Part No.	Package	Package size (mm)	Taping code	Reel size (mm)	Tape width (mm)	Basic ordering unit (pcs)	Marking
DTB713ZM	VMT3	1212	T2L	180	8	8,000	P11
DTB713ZE	EMT3	1616	TL	180	8	3,000	P11

#### •Packaging specifications

### ●Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Values	Unit
Supply voltage	V <sub>CC</sub>	-30	V
Input voltage	V <sub>IN</sub>	-10 to +5	V
Collector current	I <sub>C(MAX.)</sub> *1	-200	mA
Power dissipation	$P_{D}^{*2}$	150	mW
Junction temperature	Тj	150	°C
Range of storage temperature	T <sub>stg</sub>	-55 to +150	°C

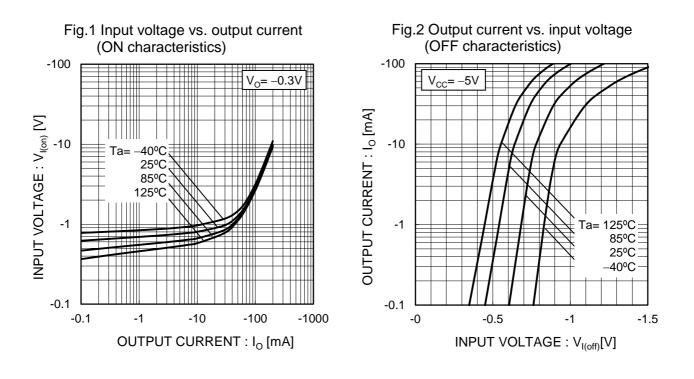
### •Electrical characteristics(Ta = 25°C)

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Input voltage	V <sub>I(off)</sub>	$V_{CC} = -5V, I_{O} = -100 \mu A$	-	-	-0.3	v
	V <sub>I(on)</sub>	$V_0 = -0.3V, I_0 = -20mA$	-2.5	-	-	V
Output voltage	V <sub>O(on)</sub>	I <sub>O</sub> / I <sub>I</sub> = -50mA / -2.5mA	-	-0.07	-0.3	V
Input current	I <sub>I</sub>	$V_1 = -5V$	-	-	-6.4	mA
Output current	I <sub>O(off)</sub>	$V_{CC} = -30V, \ V_I = 0V$	-	-	-0.5	μA
DC current gain	G <sub>I</sub>	$V_0 = -2V, I_0 = -100 \text{mA}$	140	-	-	-
Input resistance	R <sub>1</sub>	-	0.7	1.0	1.3	kΩ
Resistance ratio	R <sub>2</sub> /R <sub>1</sub>	-	8	10	12	-
Transition frequency	f <sub>T</sub> *1	V <sub>CE</sub> = -10V, I <sub>E</sub> = 5mA, f = 100MHz	-	260	-	MHz

\*1 Characteristics of built-in transistor

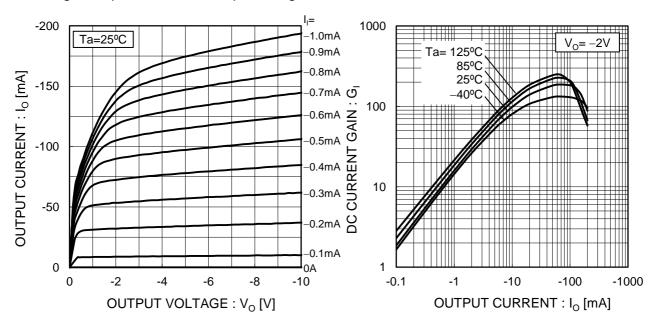
\*2 Each terminal mounted on a reference footprint

#### ●Electrical characteristic curves(Ta = 25°C)



#### Fig.3 Output current vs. output voltage

Fig.4 DC current gain vs. output current



### •Electrical characteristic curves(Ta = 25°C)

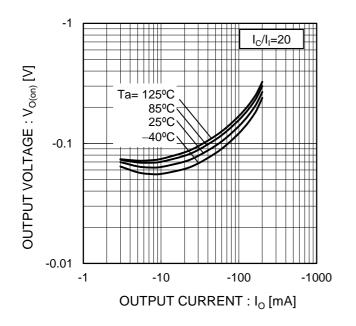
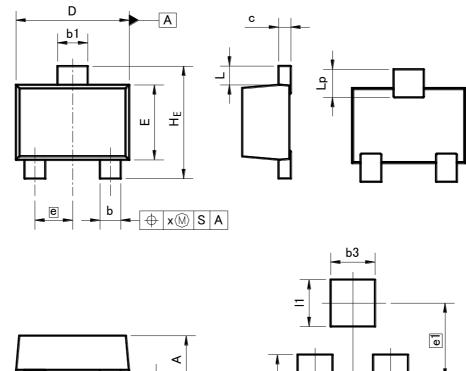
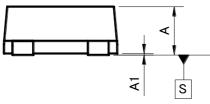


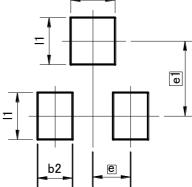
Fig.5 Output voltage vs. output current

#### •Dimensions (Unit : mm)









Pattern of terminal position areas [Not a recommended pattern of soldering pads]

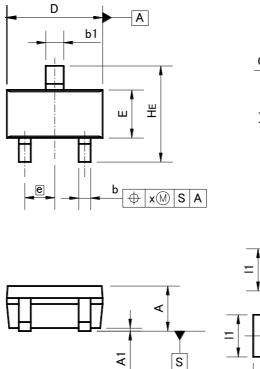
DIM	MILIM	ETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
A	0.45	0.55	0.018	0.022
A1	0.00	0.10	0.000	0.004
b	0.17	0.27	0.007	0.011
b1	0.27	0.37	0.011	0.015
с	0.08	0.18	0.003	0.007
D	1.10	1.30	0.043	0.051
E	0.70	0.90	0.028	0.035
е	0.4	40	0.0	02
HE	1.10	1.30	0.043	0.051
L	0.10	0.30	0.004	0.012
Lp	0.20	0.40	0.008	0.016
х	_	0.10	_	0.004

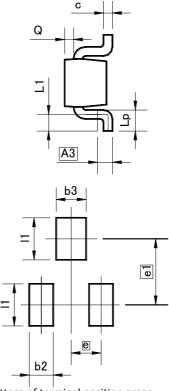
DIM	MILIM	ETERS	INCHES	
DIM	MIN	MAX	MIN	MAX
b2	-	0.37	-	0.015
b3	-	0.47	—	0.019
e1	0.80		0.0	31
1	_	0.50	_	0.020

Dimension in mm / inches

#### •Dimensions (Unit : mm)

EMT3





Pattern of terminal position areas [Not a recommended pattern of soldering pads]

	MILIM	ETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
А	0.60	0.80	0.024	0.031
A1	0.00	0.10	0.000	0.004
A3	0.:	25	0.0	10
b	0.15	0.30	0.006	0.012
b1	0.25	0.40	0.010	0.016
с	0.10	0.20	0.004	0.008
D	1.50	1.70	0.059	0.067
E	0.70	0.90	0.028	0.035
е	0.	50	0.0	20
HE	1.40	1.80	0.055	0.071
L1	0.10	-	0.004	-
Lp	0.15	_	0.006	_
Q	0.05	0.25	0.002	0.010
х	_	0.10	_	0.004

DIM	MILIM	ETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
b2	-	0.40	-	0.016
b3	-	0.50	-	0.020
e1	1.10		0.0	43
1	_	0.70	_	0.028

Dimension in mm / inches

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